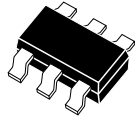


CMXD2004
SUPER-MINI
TRIPLE ISOLATED
SURFACE MOUNT
HIGH VOLTAGE
SWITCHING DIODE



SOT-26 CASE

CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD2004 type contains three (3) Isolated High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring high voltage capability. Marking code is X04.

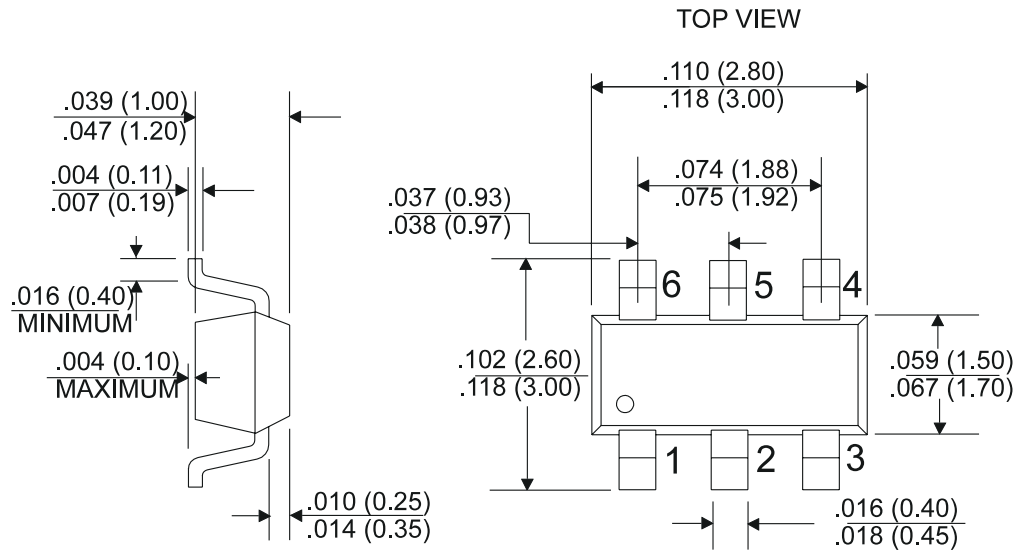
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

| | SYMBOL | | UNITS |
|--|----------------|------------|--------------------|
| Continuous Reverse Voltage | V_R | 240 | V |
| Peak Repetitive Reverse Voltage | V_{RRM} | 300 | V |
| Peak Repetitive Reverse Current | I_O | 200 | mA |
| Continuous Forward Current | I_F | 225 | mA |
| Peak Repetitive Forward Current | I_{FRM} | 625 | mA |
| Forward Surge Current, $t_p=1$ ms | I_{FSM} | 4000 | mA |
| Forward Surge Current, $t_p=1$ s | I_{FSM} | 1000 | mA |
| Power Dissipation | P_D | 350 | mW |
| Operating and Storage Junction Temperature | T_J, T_{stg} | 65 to +150 | $^\circ\text{C}$ |
| Thermal Resistance | Θ_{JA} | 357 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

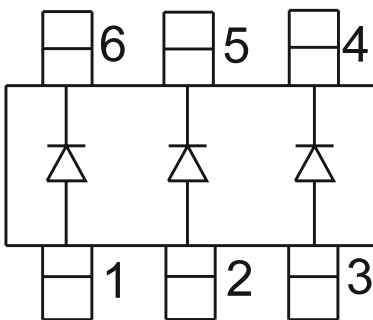
| SYMBOL | TEST CONDITIONS | MIN | MAX | UNIT |
|---------------|--|------------|------------|---------------|
| I_R | $V_R=240\text{V}$ | | 100 | nA |
| I_R | $V_R=240\text{V}, T_A=150^\circ\text{C}$ | | 100 | μA |
| BV_R | $I_R=100\mu\text{A}$ | 300 | | V |
| V_F | $I_F=100\text{mA}$ | | 1.0 | V |
| C_T | $V_R=0, f=1$ MHz | | 5.0 | pF |
| t_{rr} | $I_F=I_R=30\text{mA}$, Rec. To 3.0mA, $R_L=100\Omega$ | | 50 | ns |

MECHANICAL OUTLINE - SOT-26 CASE



All Dimensions in Inches (mm)

Pin Configuration



Lead Code

- 1) Anode 1
- 2) Anode 2
- 3) Anode 3
- 4) Cathode 3
- 5) Cathode 2
- 6) Cathode 1